

Supporting information Materials:

**Efficient interface and bulk passivation to PbS quantum dots
infrared photodetectors by PbI₂ incorporation**

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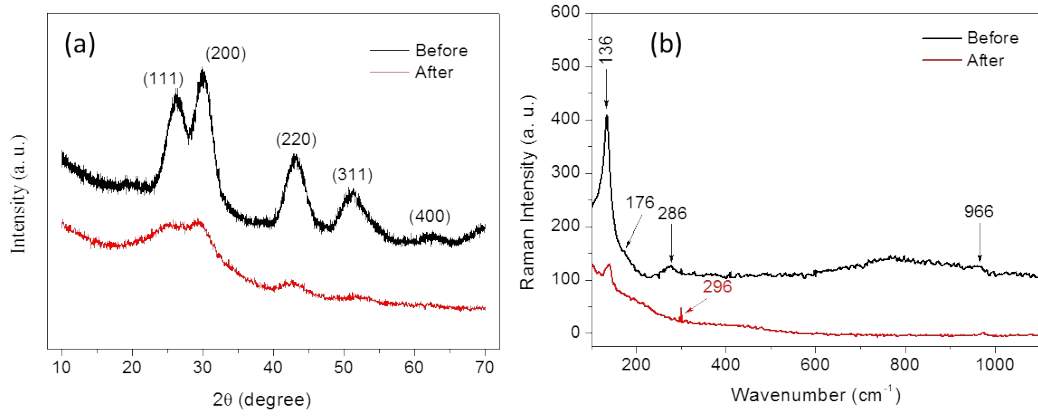


Figure s1. (a) XRD of PbS QDs before and after ligand exchange; (b) Raman of PbS QDs before and after PbI₂ treatment.

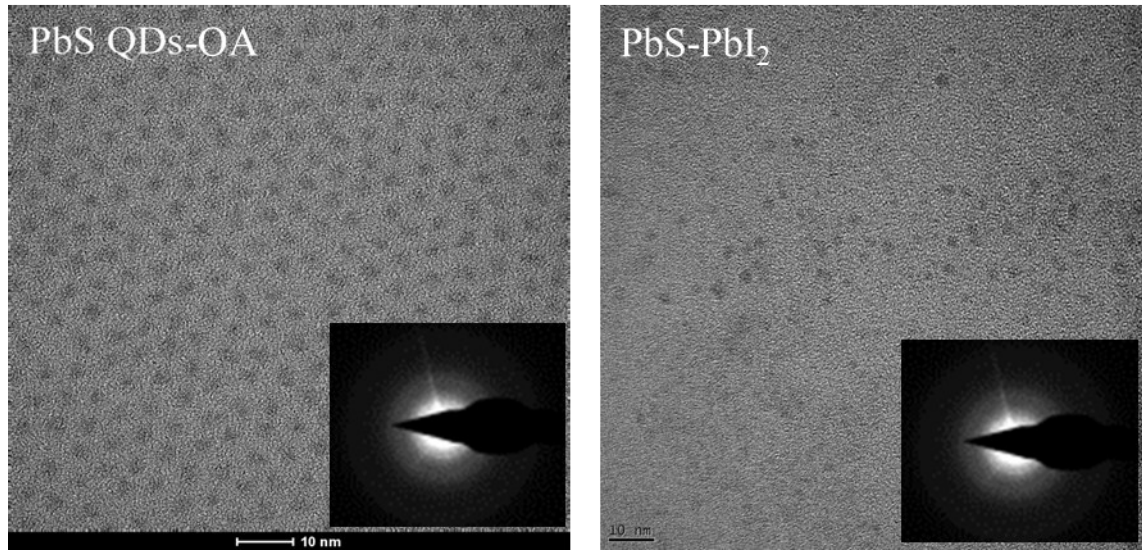


Figure s2. TEM and SAEM of QDs before (a) and after (b) PbI₂ treatment.

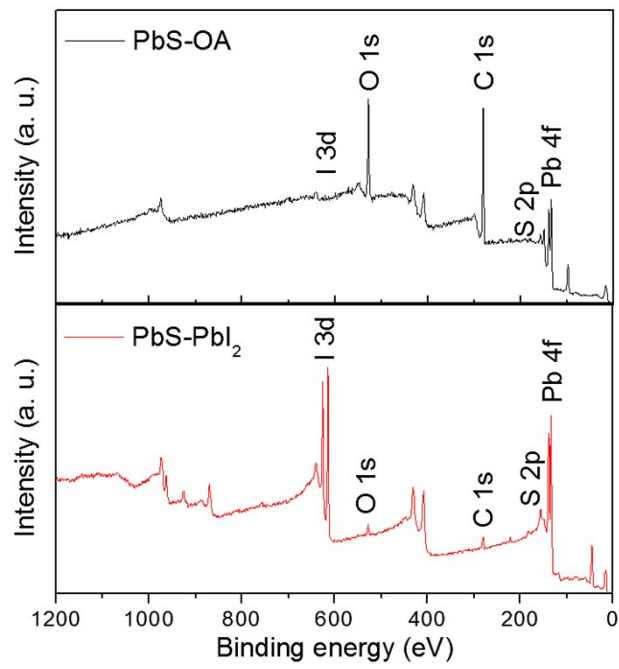


Figure s3. XPS of PbS QDs before and after PbI₂ treatment.

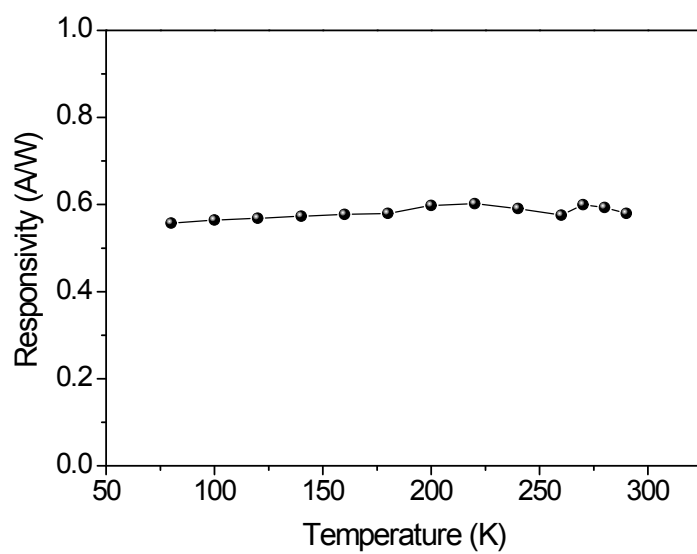


Figure s4. Temperature dependent responsivity of PbI₂ treated PbS QDs.